

Notice of References Cited

Application/Control No.

10/729,701

Applicant(s)/Patent Under
Reexamination
WEI ET AL.

Examiner

Mary C. Jacob

Art Unit

2123

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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,920,517	07-1999	Wendell, Dennis L.	365/226
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kang et al, "A Deep Sub-Micron SRAM Cell Design and Analysis Methodology, Proceedings of the 44th IEEE 2001 Midwest Symposium on Circuits and Systems, 2001
	V	Lee et al, "Static Noise Margin and Soft-Error Rate Simulations for Thin Film Transistor Cell Stability in a 4Mbit SRAM Design", IEEE International Symposium on Circuits and Systems, 1995
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.